# 捷多邦,专业PCB打档SN54AH@TG2出SN74AHCT32QUADRUPLE 2-INPUT POSITIVE-OR GATES

SCLS248I - OCTOBER 1995 - REVISED JANUARY 2000

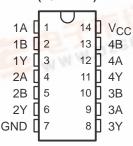
- EPIC™ (Enhanced-Performance Implanted CMOS) Process
- Inputs Are TTL-Voltage Compatible
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Standard Plastic (N) and Ceramic (J) DIPs

#### description

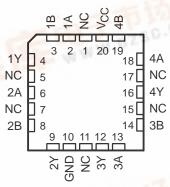
The 'AHCT32 devices are quadruple 2-input positive-OR gates. These devices perform the Boolean function  $Y = \overline{\overline{A} \bullet \overline{B}}$  or Y = A + B in positive logic.

The SN54AHCT32 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74AHCT32 is characterized for operation from –40°C to 85°C.

SN54AHCT32 . . . J OR W PACKAGE SN74AHCT32 . . . D, DB, DGV, N, OR PW PACKAGE (TOP VIEW)



SN54AHCT32 . . . FK PACKAGE (TOP VIEW)

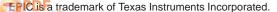


NC – No internal connection

## FUNCTION TABLE (each gate)

INPUTS		OUTPUT				
Α	В	Υ				
Н	X	Н				
X	Н	Н				
L	L	L				

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

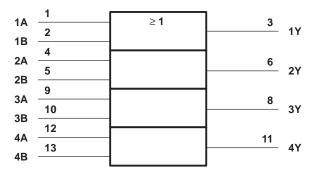




### SN54AHCT32, SN74AHCT32 QUADRUPLE 2-INPUT POSITIVE-OR GATES

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#### logic symbol†



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the D, DB, DGV, J, N, PW, and W packages.

#### logic diagram, each gate (positive logic)



### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V <sub>CC</sub>		–0.5 V to 7 V
Input voltage range, V <sub>I</sub> (see Note 1)		
Output voltage range, VO (see Note 1)		$0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Input clamp current, $I_{IK}$ ( $V_I < 0$ )		—20 mA
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0 or V <sub>O</sub> > V <sub>CO</sub>		
Continuous output current, $I_O(V_O = 0 \text{ to } V_{CC})$		
Continuous current through V <sub>CC</sub> or GND		±50 mA
Package thermal impedance, θ <sub>JA</sub> (see Note 2):	: D package	86°C/W
	DB package	96°C/W
	DGV package	127°C/W
	N package	80°C/W
	PW package	113°C/W
Storage temperature range, T <sub>stq</sub>		−65°C to 150°C

<sup>‡</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

2. The package thermal impedance is calculated in accordance with JESD 51.



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#### recommended operating conditions (see Note 3)

		SN54AHCT32		SN74AHCT32		UNIT
		MIN	MAX	MIN	MAX	UNIT
Vcc	Supply voltage	4.5	5.5	4.5	5.5	V
VIH	High-level input voltage	2		2		V
V <sub>IL</sub>	Low-level input voltage		0.8		0.8	V
VI	Input voltage	0	5.5	0	5.5	V
VO	Output voltage	0	VCC	0	VCC	V
IOH	High-level output current		-8		-8	mA
IOL	Low-level output current		8		8	mA
Δt/Δν	Input transition rise or fall rate		20		20	ns/V
T <sub>A</sub>	Operating free-air temperature	-55	125	-40	85	°C

NOTE 3: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

#### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	vcc	T <sub>A</sub> = 25°C			SN54AHCT32		SN74AHCT32		UNIT
	TEST CONDITIONS		MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNII
Vari	I <sub>OH</sub> = -50 μA	451/	4.4	4.5		4.4		4.4		V
VOH	I <sub>OH</sub> = -8 mA	4.5 V	3.94			3.8		3.8		V
Voi	I <sub>OL</sub> = 50 μA	4.5 V			0.1		0.1		0.1	V
V <sub>OL</sub>	I <sub>OL</sub> = 8 mA	4.5 V			0.36		0.44		0.44	
lį	$V_I = V_{CC}$ or GND	0 V to 5.5 V			±0.1		±1*		±1	μΑ
Icc	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			2		20		20	μΑ
∆l <sub>CC</sub> †	One input at 3.4 V, Other inputs at V <sub>CC</sub> or GND	5.5 V			1.35		1.5		1.5	mA
Ci	V <sub>I</sub> = V <sub>CC</sub> or GND	5 V		2	10				10	pF

# switching characteristics over recommended operating free-air temperature range, $V_{CC}$ = 5 V $\pm$ 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM TO (OUTPUT)	LOAD	LOAD T <sub>A</sub> = 25°C		SN54AHCT32		SN74AHCT32		UNIT		
		(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
<sup>t</sup> PLH	A or B	V	C 15 pE		5**	6.9**	1**	8**	1	8	no
t <sub>PHL</sub>		T T	C <sub>L</sub> = 15 pF		5**	6.9**	1**	8**	1	8	ns
tPLH	A or B	V	C 50 pF		5.5	7.9	1	9	1	9	
tPHL		r	$C_L = 50 pF$		5.5	7.9	1	9	1	9	ns

<sup>\*\*</sup> On products compliant to MIL-PRF-38535, this parameter is not production tested.



<sup>\*</sup> On products compliant to MIL-PRF-38535, this parameter is not production tested at  $V_{CC} = 0 \text{ V}$ . † This is the increase in supply current for each input at one of the specified TTL voltage levels rather than 0 V or  $V_{CC}$ .

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## noise characteristics, $V_{CC}$ = 5 V, $C_L$ = 50 pF, $T_A$ = 25°C (see Note 4)

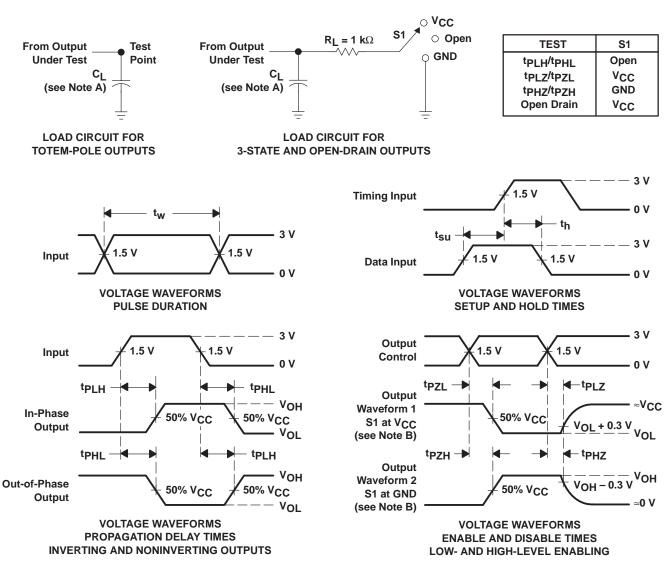
	PARAMETER		SN74AHCT32		
			TYP	MAX	UNIT
VOL(P)	Quiet output, maximum dynamic V <sub>OL</sub>		0.4	0.8	V
V <sub>OL(V)</sub>	Quiet output, minimum dynamic V <sub>OL</sub>		-0.4	-0.8	V
V <sub>OH(V)</sub>	Quiet output, minimum dynamic V <sub>OH</sub>		4.5		V
VIH(D)	High-level dynamic input voltage	2			V
V <sub>IL(D)</sub>	Low-level dynamic input voltage			0.8	V

NOTE 4: Characteristics are for surface-mount packages only.

## operating characteristics, $V_{CC}$ = 5 V, $T_A$ = 25°C

PARAMETER	TEST CONDITIONS	TYP	UNIT
C <sub>pd</sub> Power dissipation capacitance	No load, f = 1 MHz	11.5	pF

#### PARAMETER MEASUREMENT INFORMATION



NOTES: A. C<sub>I</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz,  $Z_O = 50 \Omega$ ,  $t_f \leq$  3 ns.  $t_f \leq$  3 ns.
- $\label{eq:defD} \textbf{D.} \quad \text{The outputs are measured one at a time with one input transition per measurement.}$

Figure 1. Load Circuit and Voltage Waveforms



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